

# C4D08120E

## Silicon Carbide Schottky Diode

### Z-REC<sup>®</sup> RECTIFIER

|                               |   |        |
|-------------------------------|---|--------|
| $V_{RRM}$                     | = | 1200 V |
| $I_F (T_C=135^\circ\text{C})$ | = | 12 A   |
| $Q_c$                         | = | 37 nC  |

#### Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching
- Positive Temperature Coefficient on  $V_F$

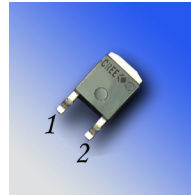
#### Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

#### Applications

- Solar Inverters
- UPS
- Motor Drives
- Power Factor Correction

#### Package



TO-252-2



| Part Number | Package  | Marking  |
|-------------|----------|----------|
| C4D08120E   | TO-252-2 | C4D08120 |

#### Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified)

| Symbol      | Parameter                                 | Value           | Unit             | Test Conditions   | Note |
|-------------|---|-----------------|------------------|---|------|
| $V_{RRM}$   | Repetitive Peak Reverse Voltage           | 1200            | V                |   |      |
| $V_{RSM}$   | Surge Peak Reverse Voltage                | 1300            | V                |   |      |
| $V_{DC}$    | DC Blocking Voltage                       | 1200            | V                |   |      |
| $I_F$       | Continuous Forward Current                | 24.5<br>12<br>8 | A                | $T_C=25^\circ\text{C}$<br>$T_C=135^\circ\text{C}$<br>$T_C=155^\circ\text{C}$  |      |
| $I_{FRM}$   | Repetitive Peak Forward Surge Current     | 38<br>26        | A                | $T_C=25^\circ\text{C}$ , $t_p=10$ ms, Half Sine pulse<br>$T_C=110^\circ\text{C}$ , $t_p=10$ ms, Half Sine pulse     |      |
| $I_{FSM}$   | Non-Repetitive Peak Forward Surge Current | 64<br>50        | A                | $T_C=25^\circ\text{C}$ , $t_p=10$ ms, Half Sine pulse<br>$T_C=110^\circ\text{C}$ , $t_p=10$ ms, Half Sine pulse     |      |
| $I_{F,Max}$ | Non-Repetitive Peak Forward Current       | 600<br>480      | A                | $T_C=25^\circ\text{C}$ , $t_p=10$ $\mu\text{s}$ , Pulse<br>$T_C=110^\circ\text{C}$ , $t_p=10$ $\mu\text{s}$ , Pulse |      |
| $P_{tot}$   | Power Dissipation                         | 137<br>59       | W                | $T_C=25^\circ\text{C}$<br>$T_C=110^\circ\text{C}$   |      |
| $T_j$       | Operating Junction Range                  | -55 to<br>+175  | $^\circ\text{C}$ |   |      |
| $T_{stg}$   | Storage Temperature Range                 | -55 to<br>+135  | $^\circ\text{C}$ |   |      |

## Electrical Characteristics

| Symbol | Parameter               | Typ.            | Max.       | Unit          | Test Conditions  | Note |
|--------|-------------------------|-----------------|------------|---------------|--|------|
| $V_F$  | Forward Voltage         | 1.5<br>2.2      | 1.8<br>3   | V             | $I_F = 2\text{ A}$ $T_J = 25^\circ\text{C}$<br>$I_F = 2\text{ A}$ $T_J = 175^\circ\text{C}$  |      |
| $I_R$  | Reverse Current         | 35<br>100       | 250<br>350 | $\mu\text{A}$ | $V_R = 1200\text{ V}$ $T_J = 25^\circ\text{C}$<br>$V_R = 1200\text{ V}$ $T_J = 175^\circ\text{C}$  |      |
| $Q_C$  | Total Capacitive Charge | 37              |            | nC            | $V_R = 800\text{ V}$ , $I_F = 2\text{ A}$<br>$di/dt = 200\text{ A}/\mu\text{s}$<br>$T_J = 25^\circ\text{C}$  |      |
| C      | Total Capacitance       | 560<br>37<br>27 |            | pF            | $V_R = 0\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$<br>$V_R = 400\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$<br>$V_R = 800\text{ V}$ , $T_J = 25^\circ\text{C}$ , $f = 1\text{ MHz}$ |      |

Note:

1. This is a majority carrier diode, so there is no reverse recovery charge.

## Thermal Characteristics

| Symbol          | Parameter   | Typ. | Unit                      |
|-----------------|---|------|---------------------------|
| $R_{\theta JC}$ | TO-252 Package Thermal Resistance from Junction to Case | 1.1  | $^\circ\text{C}/\text{W}$ |

## Typical Performance

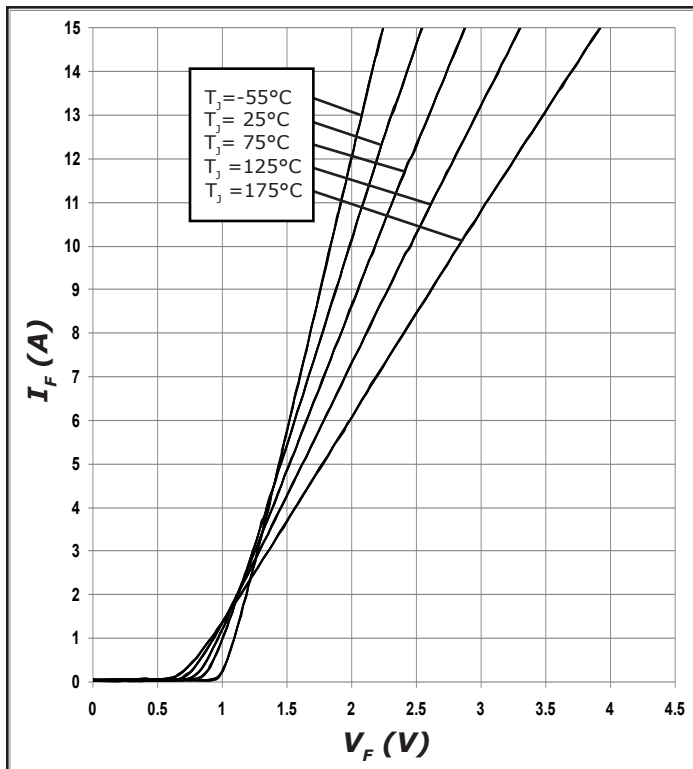


Figure 1. Forward Characteristics

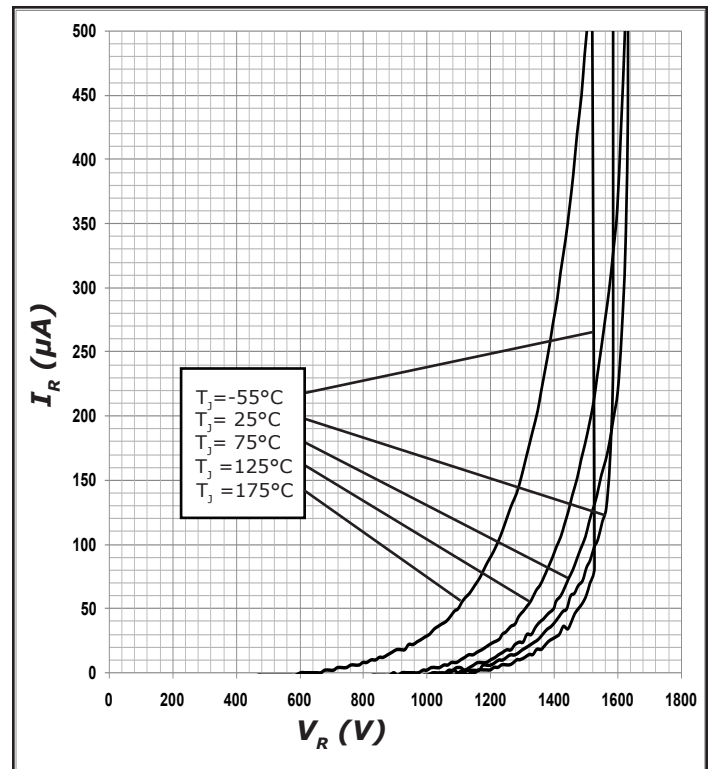


Figure 2. Reverse Characteristics

## Typical Performance

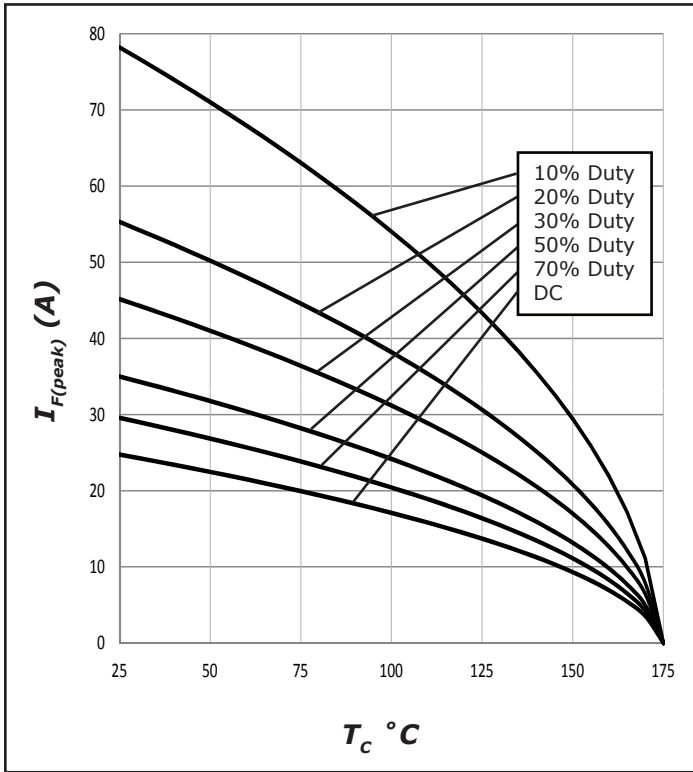


Figure 3. Current Derating

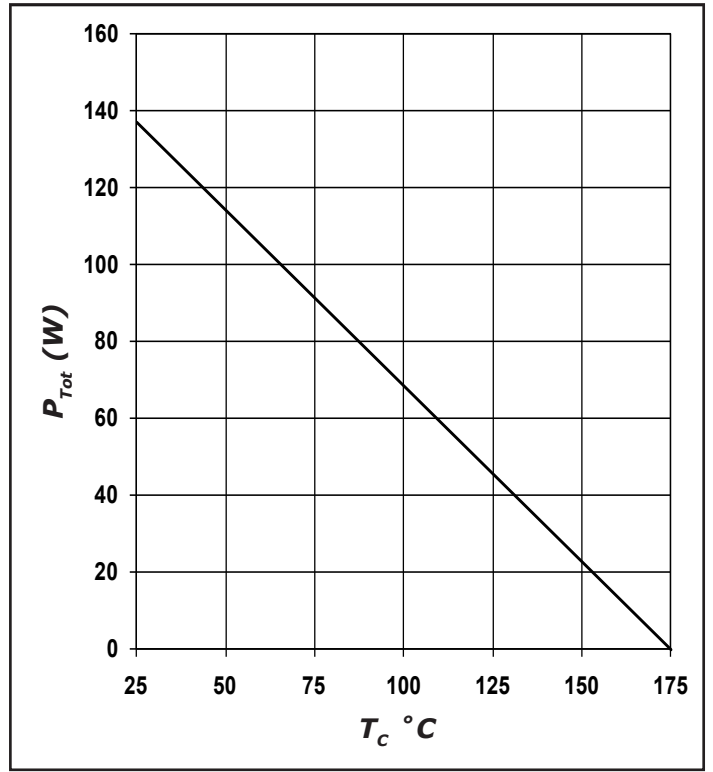


Figure 4. Power Derating

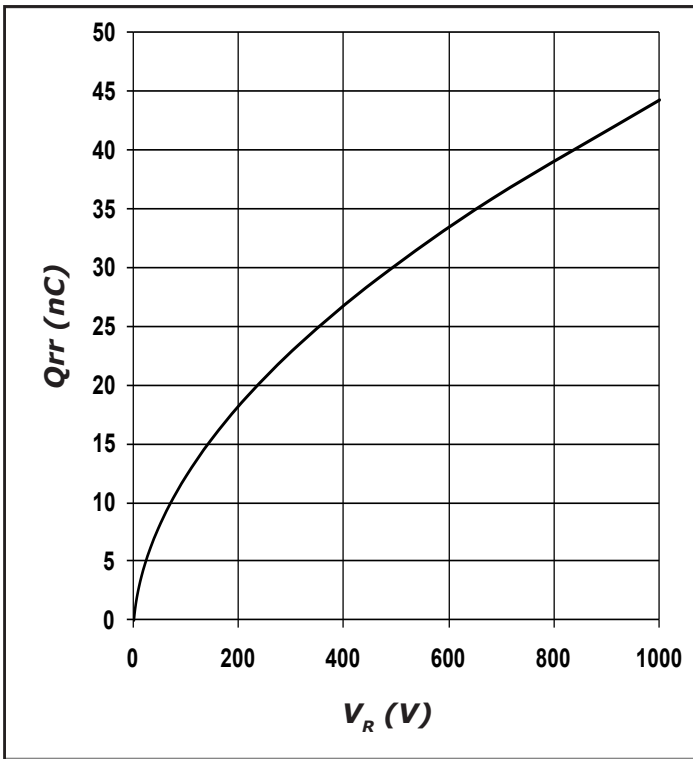


Figure 5. Recovery Charge vs. Reverse Voltage

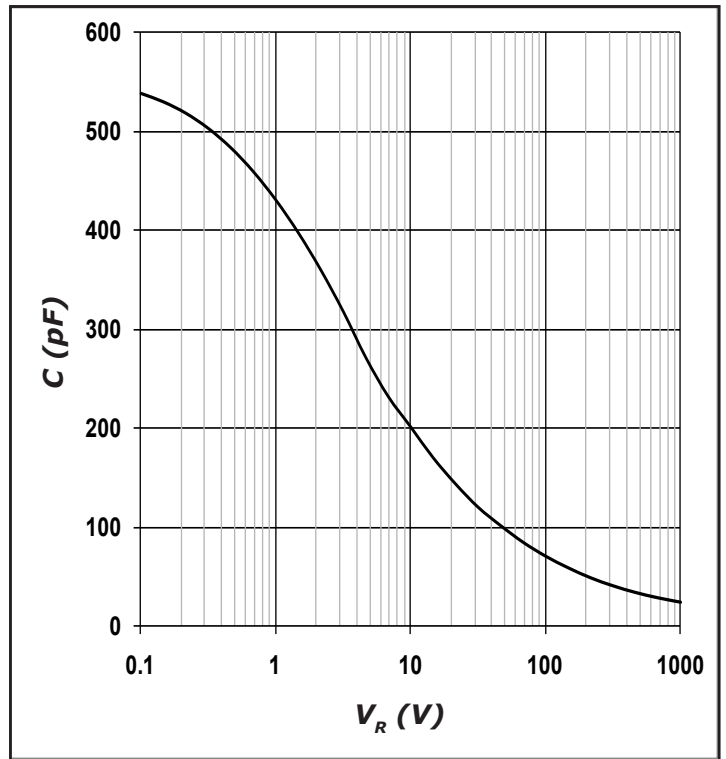


Figure 6. Capacitance vs. Reverse Voltage

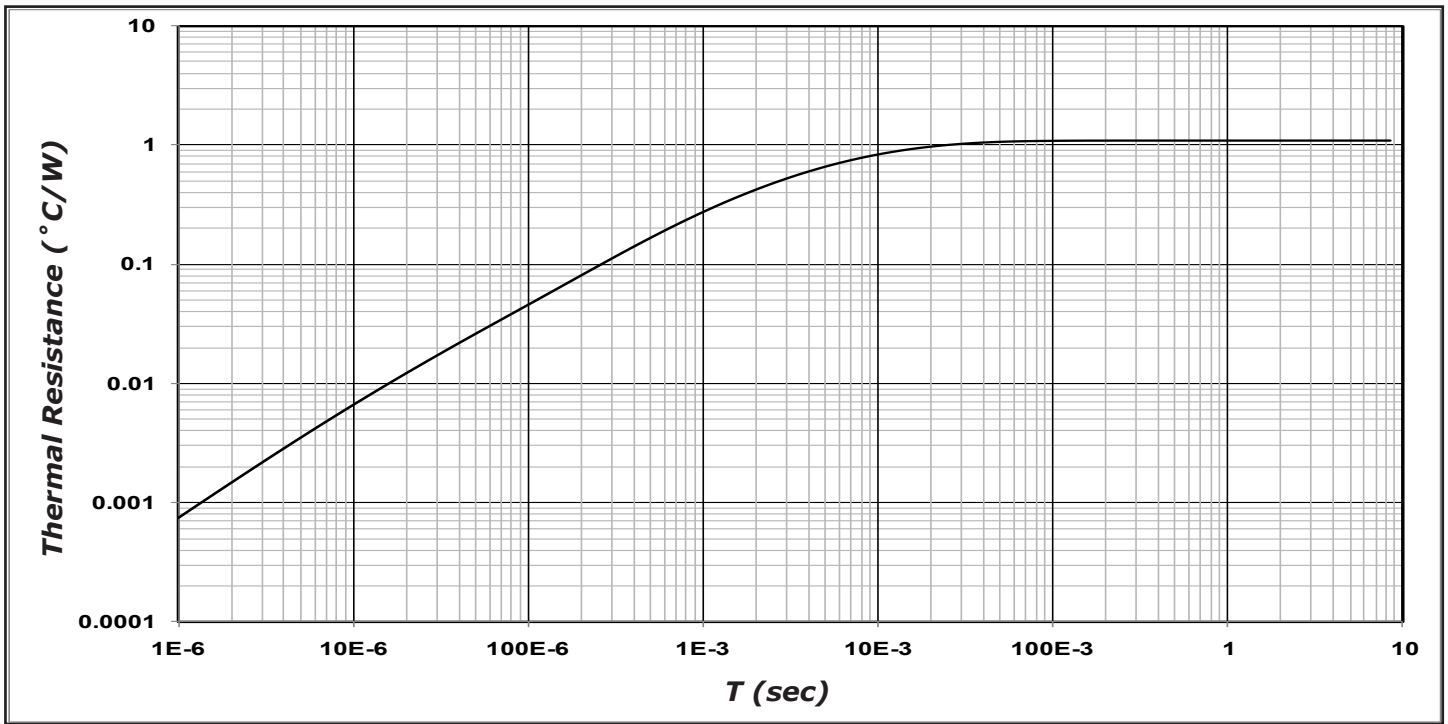
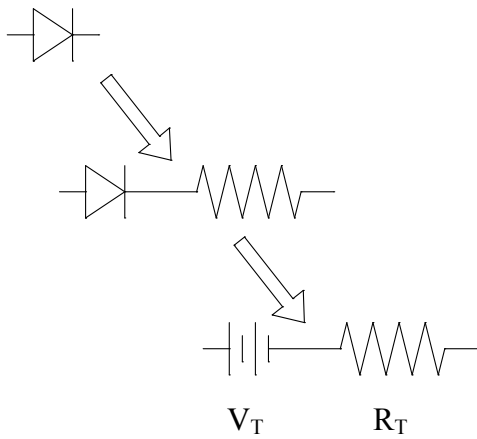


Figure 7. Transient Thermal Impedance

## Diode Model



$$V_{fT} = V_T + I_f * R_T$$

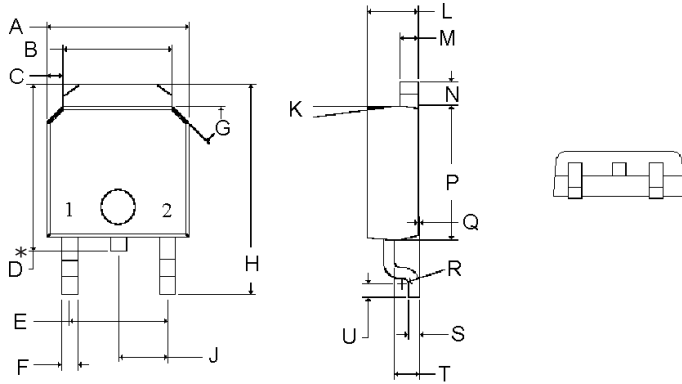
$$V_T = 0.96 + (T_j * -2.1 * 10^{-3})$$

$$R_T = 0.06 + (T_j * 8.0 * 10^{-4})$$

Note:  $T_j$  = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

## Package Dimensions

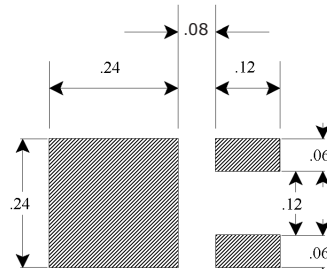
Package TO-252-2



| POS | Inches     |      | Millimeters |        |
|-----|------------|------|-------------|--------|
|     | Min        | Max  | Min         | Max    |
| A   | .250       | .289 | 6.350       | 7.341  |
| B   | .197       | .215 | 5.004       | 5.461  |
| C   | .027       | .050 | .686        | 1.270  |
| D*  | .270       | .322 | 6.858       | 8.179  |
| E   | .178       | .182 | 4.521       | 4.623  |
| F   | .025       | .045 | .635        | 1.143  |
| G   | 44°        | 46°  | 44°         | 46°    |
| H   | .380       | .410 | 9.652       | 10.414 |
| J   | .090 TYP   |      | 2.286 TYP   |        |
| K   | 6°         | 8°   | 6°          | 8°     |
| L   | .086       | .094 | 2.184       | 2.388  |
| M   | .018       | .034 | .457        | .864   |
| N   | .035       | .050 | .889        | 1.270  |
| P   | .231       | .246 | 5.867       | 6.248  |
| Q   | 0.00       | .005 | 0.00        | .127   |
| R   | R0.010 TYP |      | R0.254 TYP  |        |
| S   | .017       | .023 | .432        | .584   |
| T   | .038       | .045 | .965        | 1.143  |
| U   | .021       | .029 | .533        | .737   |

Note:  
\* Tab "D" may not be present

## Recommended Solder Pad Layout



TO-252-2

| Part Number | Package  | Marking  |
|-------------|----------|----------|
| C4D05120E   | TO-252-2 | C4D05120 |

Note: Recommended soldering profiles can be found in the applications note here:  
[http://www.cree.com/power\\_app\\_notes/soldering](http://www.cree.com/power_app_notes/soldering)





## Notes

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- **RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Cree representative or from the Product Documentation sections of [www.cree.com](http://www.cree.com).

- **REACH Compliance**

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a Cree representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

- This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control systems.